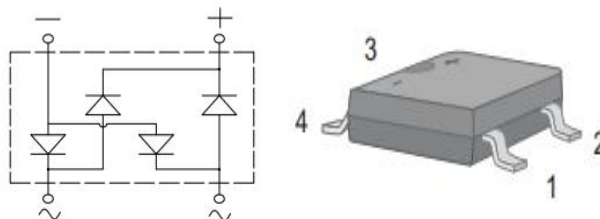


**Bridge Rectifier Diode 整流桥**

■ **Features 特点**

Glass passivated chip junction 玻璃钝化结  
High surge current capability 高浪涌电流能力  
Reflow Solder Temperature 220°C 回流焊温度 220 度  
Package 封装: MBS



■ **Maximum Rating 最大额定值**

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	MB05SA	MB1SA	MB2SA	MB4SA	MB6SA	MB8SA	MB10SA	Unit 单位
Marking 印字		MB05S	MB1S	MB2S	MB4S	MB6S	MB8S	MB10S	
Peak Reverse Voltage 反向峰值电压	$V_{RRM}$	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_{R(DC)}$	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	$I_F$	1							A
Peak Surge Current 峰值浪涌电流	$I_{FSM}$	30							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	75							$^{\circ}\text{C/W}$
Junction Temperature 结温	$T_J$	150							$^{\circ}\text{C}$
Storage Temperature 储藏温度	$T_{stg}$	-55to+150 $^{\circ}\text{C}$							

■ **Electrical Characteristics 电特性**

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压降	$V_F$		1.0		V	$I_F=0.5\text{A}$
Reverse Current ( $T_A=25^{\circ}\text{C}$ ) 反向漏电流( $T_A=125^{\circ}\text{C}$ )	$I_R$			5 500	$\mu\text{A}$	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	$C_D$		13		pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

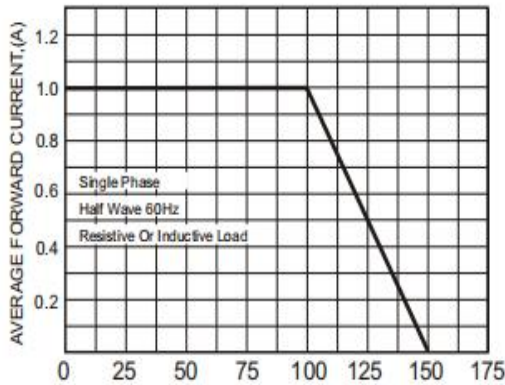


Figure 1: Forward Current Derating Curve

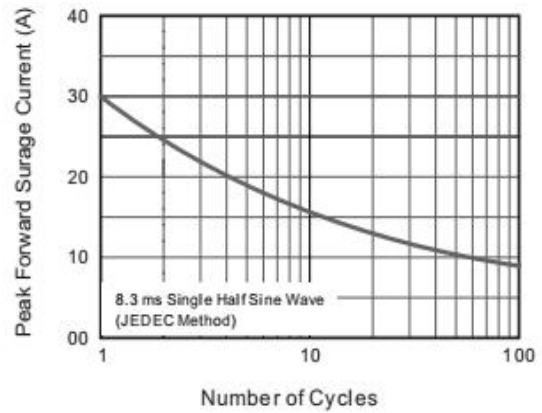


Figure 2: Peak Forward Surge Current

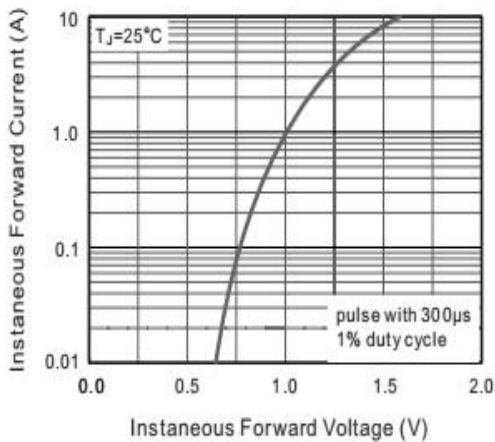


Figure 3: Instantaneous Forward Characteristics

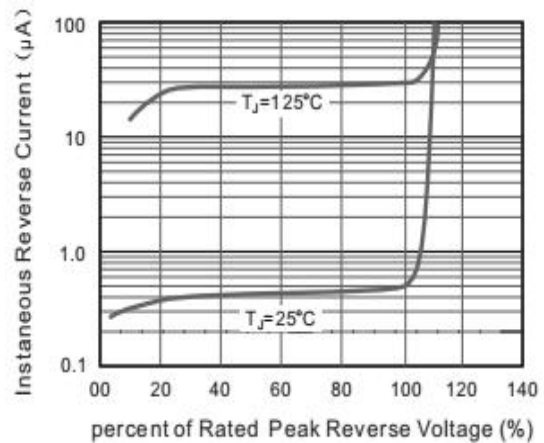
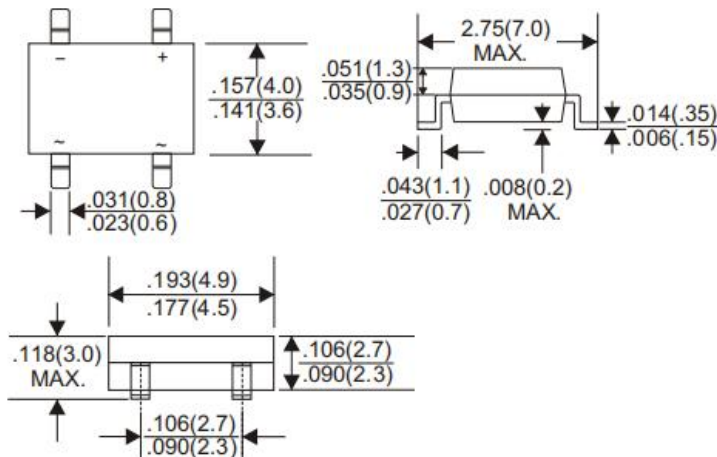


Figure 4: Reverse Leakage Characteristics

■ Dimension 外形封装尺寸



Dimensions in inches and (millimeters)